



6A, 600V Hyperfast Diodes

The RHRD660S9A_F085 is hyperfast diodes with soft recovery characteristics ($t_{rr} < 30\text{ns}$). It has half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49057.

Ordering Information

| PART NUMBER | PACKAGE | BRAND |
|-----------------|---------|--------|
| RHRD660S9A_F085 | TO-252 | RHR660 |

Features

- Hyperfast with Soft Recovery <30ns
- Operating Temperature 175°C
- Reverse Voltage Up To 600V
- Avalanche Energy Rated
- Planar Construction

Applications

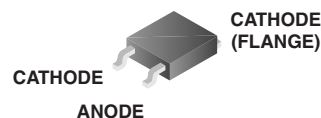
- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

Symbol



JEDEC STYLE TO-252



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

| | RHRD660S9A_F085 | UNITS |
|--|---------------------------|-------|
| Peak Repetitive Reverse Voltage | V_{RRM} 600 | V |
| Working Peak Reverse Voltage | V_{RWM} 600 | V |
| DC Blocking Voltage | V_R 600 | V |
| Average Rectified Forward Current ($T_C = 152^\circ\text{C}$) | $I_{F(AV)}$ 6 | A |
| Repetitive Peak Surge Current (Square Wave, 20kHz) | I_{FRM} 12 | A |
| Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz) | I_{FSM} 60 | A |
| Maximum Power Dissipation | P_D 50 | W |
| Avalanche Energy (See Figures 10 and 11) | E_{AVL} 10 | mJ |
| Operating and Storage Temperature | T_{STG}, T_J -65 to 175 | °C |
| Maximum Lead Temperature for Soldering (Leads at 0.063 in. (1.6mm) from case for 10s) | T_L 300 | °C |
| Package Body for 10s, see Tech Brief 334. | T_{PKG} 260 | °C |

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

| SYMBOL | TEST CONDITION | MIN | TYP | MAX | UNITS |
|-----------------|---|-----|-----|-----|---------------------------|
| V_F | $I_F = 6\text{A}$ | - | - | 2.1 | V |
| | $I_F = 6\text{A}$, $T_C = 150^\circ\text{C}$ | - | - | 1.7 | V |
| I_R | $V_R = 600\text{V}$ | - | - | 100 | μA |
| | $V_R = 600\text{V}$, $T_C = 150^\circ\text{C}$ | - | - | 500 | μA |
| t_{rr} | $I_F = 1\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$ | - | - | 30 | ns |
| | $I_F = 6\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$ | - | - | 35 | ns |
| t_a | $I_F = 6\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 16 | - | ns |
| t_b | $I_F = 6\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 8.5 | - | ns |
| Q_{RR} | $I_F = 6\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$ | - | 45 | - | nC |
| C_J | $V_R = 10\text{V}$, $I_F = 0\text{A}$ | - | 20 | - | pF |
| $R_{\theta JC}$ | | - | - | 3 | $^\circ\text{C}/\text{W}$ |

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 9).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

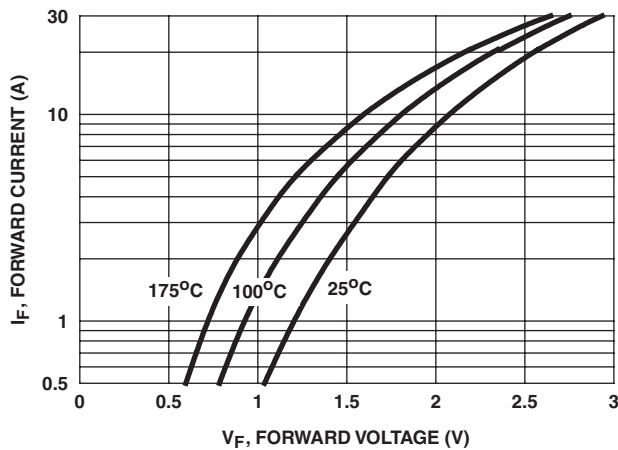


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

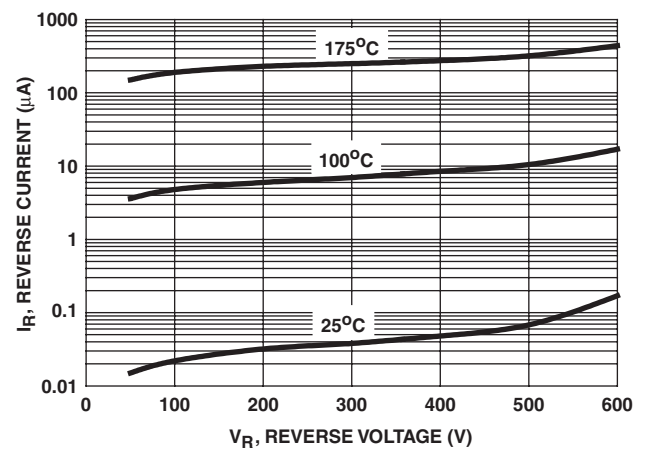


FIGURE 2. REVERSE CURRENT vs REVERSE